



DMP3050LVT

#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
00)/	50mΩ @ V <sub>GS</sub> = -10V	-4.5A
-30V	75mΩ @ V <sub>GS</sub> = -4.5V	-3.7A

### Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

### **Features**

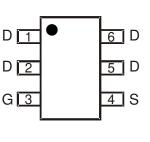
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

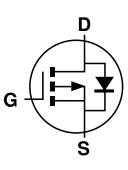
- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013grams (Approximate)



Top View



**Device Schematic** 





### Ordering Information (Note 4)

Part Number	Case	Packaging				
DMP3050LVT-7	TSOT26	3000/Tape & Reel				
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.						

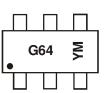
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



G64 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$ = Year (ex: D = 2016) M = Month (ex: 9 = September)

Date Code Key												
Year	2011		~	2016	2017	20	)18	2019	2020	20	21	2022
Code	Y		~	D	E		F	G	Н		I	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	-30	V	
Gate-Source Voltage (Note 5)		V <sub>GSS</sub>	±25	V	
Continuous Drain Current (Note 6) V 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-4.5 -3.5	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-5.2 -4.1	A
Maximum Continuous Body Diode Forward Curren	t (Note 6)	ls	-2	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	6)	I <sub>DM</sub>	-25	А	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	D	1.6	W	
Total Fower Dissipation (Note 6)	T <sub>A</sub> = +70°C	PD	1.0	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Р	78	°C/W	
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{ extsf{ heta}JA}$	49		
Thermal Resistance, Junction to Case (Note 6) Steady State		$R_{\theta JC}$	13		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

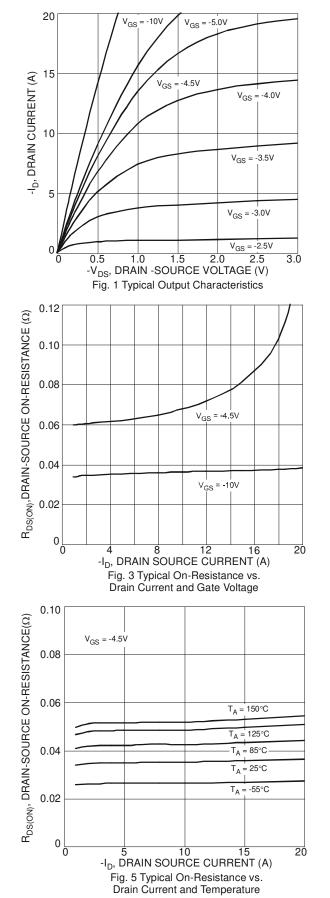
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

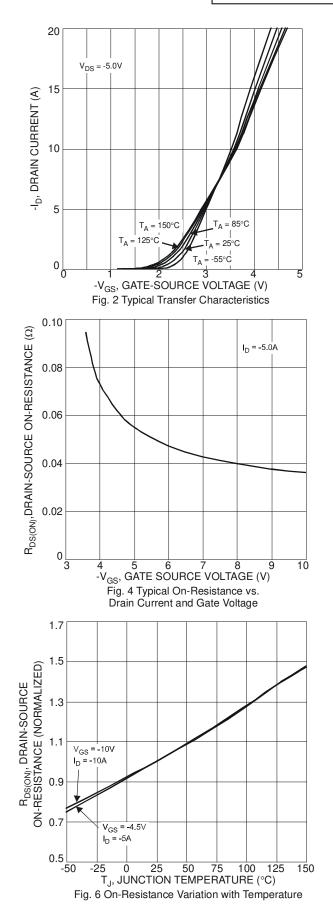
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-	-2.0	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$
Static Drain-Source On-Resistance	Proven	-	36	50	mΩ	$V_{GS} = -10V, I_D = -4.5A$
	R <sub>DS(ON)</sub>	-	56	75	1115.2	$V_{GS} = -4.5V, I_D = -3A$
Forward Transfer Admittance	Y <sub>fs</sub>	-	7.2	-	S	$V_{DS} = -5V, I_D = -5A$
Diode Forward Voltage	V <sub>SD</sub>	-	-0.7	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	-	620	-	рF	
Output Capacitance	C <sub>oss</sub>	-	83	-	рF	−V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V, −f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	62	-	pF	1 - 1.00012
Gate Resistance	R <sub>g</sub>	-	10.8	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	-	5.1	-	nC	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	-	10.5	-	nC	V <sub>DS</sub> = -15V, I <sub>D</sub> = -6A
Gate-Source Charge	Q <sub>gs</sub>	-	1.8	-	nC	$v_{\rm DS} = -15 v, 1_{\rm D} = -6A$
Gate-Drain Charge	Q <sub>gd</sub>	-	1.9	-	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	-	6.8	-	ns	
Turn-On Rise Time	t <sub>R</sub>	-	4.9	-	ns	$V_{DD} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	28.4	-	ns	$R_g = 6\Omega, I_D = -1A$
Turn-Off Fall Time	t <sub>F</sub>	-	12.4	-	ns	

Notes:

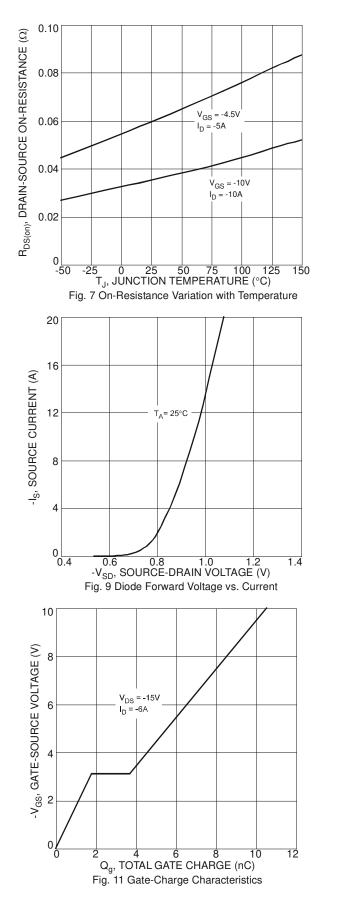
5. AEC-Q101 V<sub>GS</sub> maximum is ±20V.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

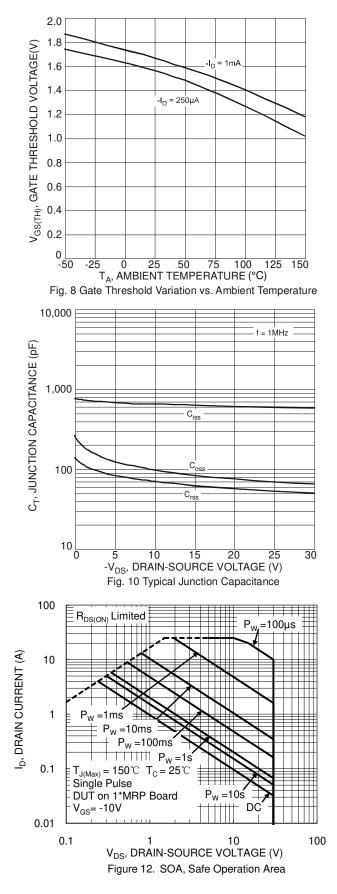






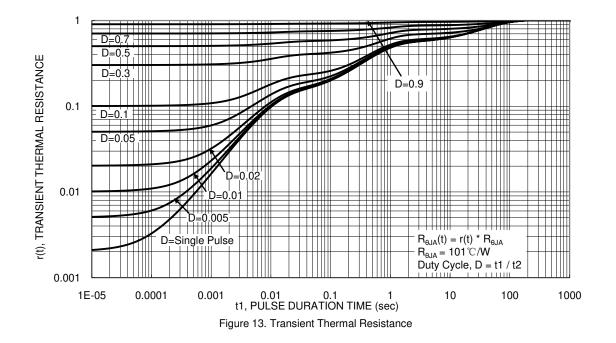








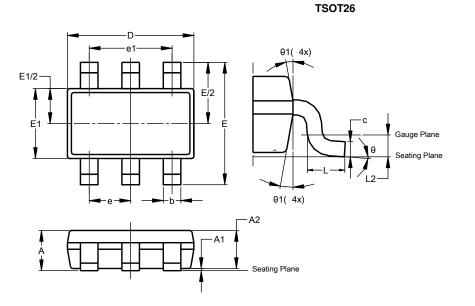






# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

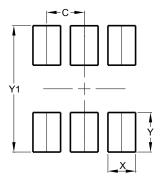


TSOT26							
Dim	Min	Max	Тур				
Α	-	1.00	-				
A1	0.010	0.100	-				
A2	0.840	0.900	-				
D	2.800	3.000	2.900				
Е	2	.800 BS	С				
E1	1.500	1.700	1.600				
b	0.300	0.450	-				
С	0.120	0.200	-				
е	0.950 BSC						
e1	1	1.900 BSC					
L	0.30	0.50	-				
L2	0.250 BSC						
θ	0°	8°	4°				
θ1	4°	12°	-				
Α	All Dimensions in mm						

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSOT26



Dimensions	Value (in mm)			
С	0.950			
Х	0.700			
Y	1.000			
Y1	3.199			



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